

YAO-3950

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a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a passivation layer provided so as to cover the second interconnect, wherein the second interconnect is provided on the second interlayer insulating film so as to cover at least a part of the capacitor.

32. (As Amended) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode;

a first interlayer insulating film provided so as to directly cover the capacitor, the first interlayer insulating film having a tensile stress;

a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film;

a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a passivation layer provided so as to cover the second interconnect, wherein the second interconnect is provided on the second interlayer insulating film so as to cover at least a part of the capacitor.

Please add claims 33-34:

33. (Newly Added) A semiconductor device, comprising:

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a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode, said dielectric film being formed from either a dielectric material having a high dielectric constant or a ferroelectric material;

a first interlayer insulating film provided so as to directly cover the capacitor;

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a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a first contact hole formed in the first interlayer insulating film;

a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film; and

a passivation layer provided so as to cover the second interconnect; and

a hydrogen supplying layer provided between the first interconnect and the second interlayer insulating film excluding an area in which the capacitor is provided.

34. (Newly Added) A semiconductor device, comprising:

a capacitor provided on a supporting substrate having an integrated circuit thereon and including a lower electrode, a dielectric film, and an upper electrode;

a first interlayer insulating film provided so as to directly cover the capacitor, the first interlayer insulating film having a tensile stress;

a first interconnect selectively provided on the first interlayer insulating film and electrically connected to the integrated circuit and the capacitor through a contact hole formed in the first interlayer insulating film;

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a second interlayer insulating film having a tensile stress provided so as to directly cover the first interconnect and the first interlayer insulating film;

a second interconnect selectively provided on the second interlayer insulating film and electrically connected to the first interconnect through a second contact hole formed in the second interlayer insulating film;

D3 a passivation layer provided so as to cover the second interconnect;

and

a hydrogen supplying layer provided between the first interconnect and the second interlayer insulating film excluding an area in which the capacitor is provided.

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